

SOT-227 Power Module Single Switch - Power MOSFET, 420 A



PRIMARY CHARACTERISTICS				
V_{DSS}	100 V			
R _{DS(on)}	1.3 mΩ			
I _D ⁽¹⁾	330 A at 90 °C			
Туре	Modules - MOSFET			
Package	SOT-227			

FEATURES

- $I_D > 420 \text{ A}, T_C = 25 \, ^{\circ}\text{C}$
- TrenchFET® power MOSFET
- Low input capacitance (Ciss)
- · Reduced switching and conduction losses
- Ultra low gate charge (Qa)
- Avalanche energy rated (UIS)
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free

RoHS
COMPLIANT

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
MOSFET					
Drain to source voltage	V_{DSS}		100	V	
Continuous dusin surrent // st 10.1/		T _C = 25 °C	435		
Continuous drain current, V _{GS} at 10 V	I _D	T _C = 90 °C	330	Α	
Pulsed drain current	I _{DM} ⁽¹⁾		1130		
Power dissipation	P_D	T _C = 25 °C	652	W	
Gate to source voltage	V _{GS}		± 20	V	
Single pulse avalanche energy	E _{AS}	$T_{C} = 25 ^{\circ}\text{C}, L = 10 \text{mH}, V_{GS} = 10 \text{V}$	11 500	mJ	
Single pulse avalanche current	I _{AS}	$T_C = 25 ^{\circ}\text{C}, L = 10 \text{mH}, V_{GS} = 10 \text{V}$	48	А	
MODULE					
Insulation voltage (RMS)	V _{ISOL}	any terminal to case, t = 1 min	2500	V	
Operating junction temperature range	T_J		-55 to +175	°C	

Notes

⁽¹⁾ Limited at maximum junction temperature



THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction and storage tem	perature range	T_J , T_{Stg}		-55	-	175	ပ္
Junction to case	MOSFET	R_{thJC}		-	-	0.23	°C/W
Case to heat sink	Module	R _{thCS}	Flat, greased surface	-	0.1	-	C/VV
Weight				-	30	-	g
Mounting torque			Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque			Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style					5	SOT-227	

ELECTRICAL CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain to source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 750 \mu\text{A}$	100	-	-	V
Static drain to source on-resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 200 A	-	1.3	2.15	mΩ
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 750 \mu A$	2.2	2.9	3.8	V
Forward transconductance	9 _{fs}	$V_{DS} = 20 \text{ V}, I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}$	-	94	-	S
Duain to accuracy looks are accurant		V _{DS} = 100 V, V _{GS} = 0 V	-	0.6	4	
Drain to source leakage current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V, T _J = 125 °C	-	32	-	μA
Gate to source leakage	I _{GSS}	V _{GS} = ± 20 V	-	-	± 350	nA
Total gate charge	Qg	I _D = 200 A	-	375	-	
Gate to source charge	Q _{gs}	V _{DS} = 50 V		84	-	nC
Gate to drain ("Miller") charge	Q _{gd}			138	-	1
Turn-on delay time	t _{d(on)}	V _{DD} = 50 V	-	45	-	
Rise time	t _r	I _D = 100 A	-	275	-	
Turn-off delay time	t _{d(off)}	$R_g = 1.2 \Omega$	-	152	-	ns
Fall time	t _f	V _{GS} = 10 V	-	172	-	
Input capacitance	C _{iss}	V _{GS} = 0 V	-	17.3	-	
Output capacitance	C _{oss}	V _{DS} = 25 V	-	9.2	-	nF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	-	0.9	-	

SOURCE-DRAIN RATINGS AND CHARACTERISTICS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Continuous source current (body diode)	I _S	MOSFET symbol	-	-	435	
Pulsed source current (body diode)	I _{SM}	showing the integral reverse p-n junction diode	-	-	1130	А
Diode forward voltage	V _{SD}	I _S = 200 A, V _{GS} = 0 V	-	0.91	1.5	V
Reverse recovery time	t _{rr}	T 05 00 1 1 50 4	-	171	-	ns
Reverse recovery charge	Q _{rr}	$T_J = 25 ^{\circ}\text{C}, I_F = I_S = 50 \text{A},$ $dI/dt = 100 \text{A/}\mu\text{s}, V_R = 50 \text{V}$	-	740	-	nC
Reverse recovery current	I _{RM}	α, αι = 1007 τμο, τη = 00 τ	-	8.7	-	Α



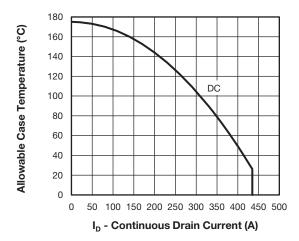


Fig. 1 - Maximum Continuous Drain Current vs. Case Temperature

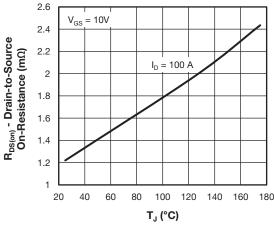


Fig. 4 - Typical Drain-to-Source On-Resistance vs. Temperature

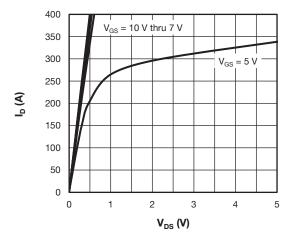


Fig. 2 - Typical Drain to Source Current Output Characteristics at $T_{J}=25\ ^{\circ}\text{C}$

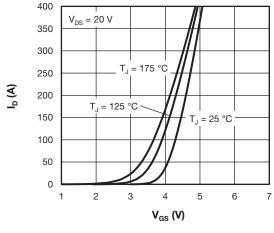


Fig. 5 - Typical Transfer Characteristics

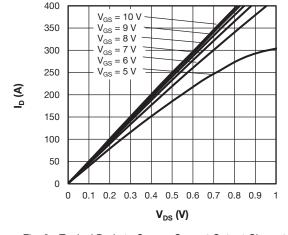


Fig. 3 - Typical Drain to Source Current Output Characteristics at $T_{J} = 125\ ^{\circ}\text{C}$

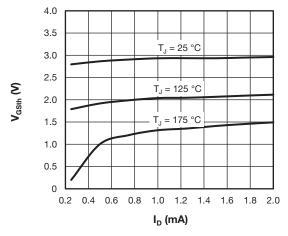


Fig. 6 - Typical Gate Threshold Voltage Characteristics

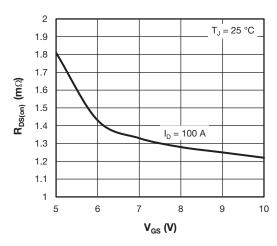


Fig. 7 - Typical Drain-State Resistance vs. Gate-to-Source Voltage

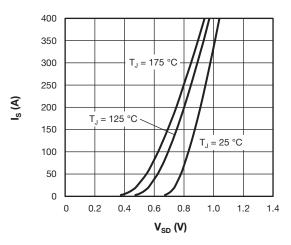


Fig. 8 - Typical Body Diode Source-to-Drain Current Characteristics

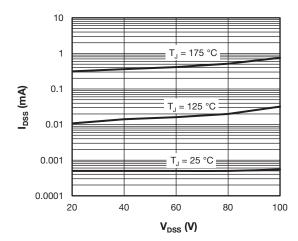


Fig. 9 - Typical Zero Gate Voltage Drain Current

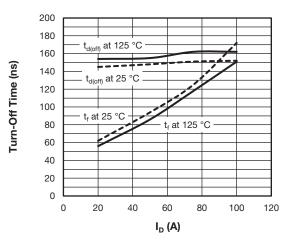


Fig. 10 - Typical Turn off Switching Time vs. I_d $V_{DD}=50$ V, $R_g=1.2~\Omega,\,V_{GS}=\pm~10$ V, $L=500~\mu H$

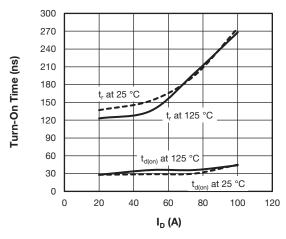


Fig. 11 - Typical Turn-on Switching Time vs. I_d V_{DD} = 50 V, R_q = 1.2 Ω , V_{GS} = \pm 10 V, L = 500 μ H

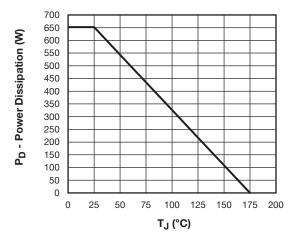


Fig. 12 - Power Dissipation Curve



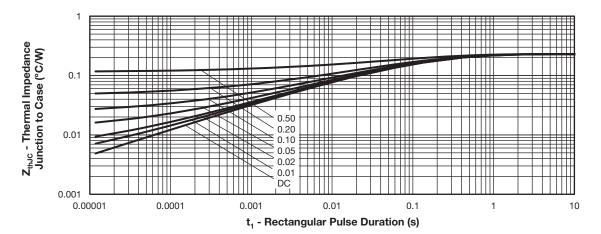


Fig. 13 - Maximum Thermal Impedance Junction-to-Case Characteristics

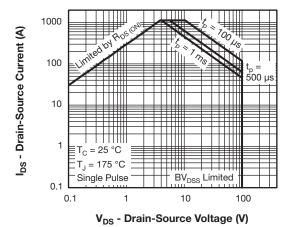
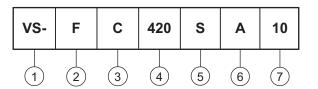


Fig. 14 - Safe Operating Area

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - MOSFET module

MOSFET die generation

4 - Current rating (420 = 420 A)

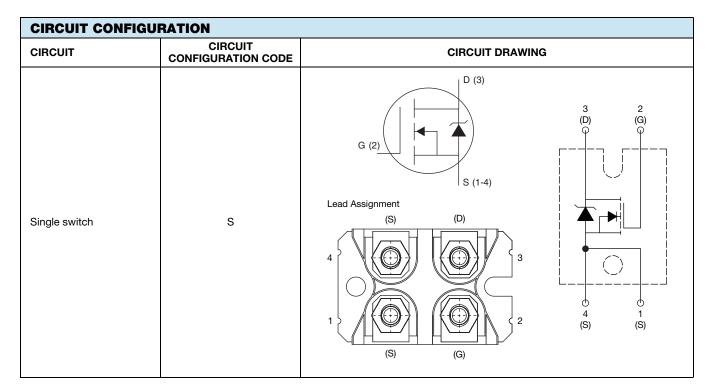
5 - Circuit configuration (S = single switch)

6 - Package indicator (SOT-227 standard insulated base)

7 - Voltage rating (10 = 100 V)

Quantity per tube is 10, M4 screw and washer included



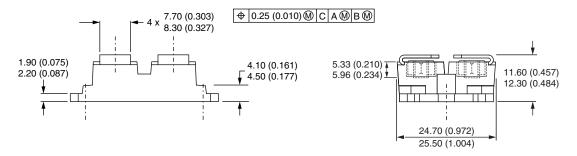


LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95423			
Packaging information	www.vishay.com/doc?95425			

SOT-227 Generation 2

DIMENSIONS in millimeters (inches)





Note

· Controlling dimension: millimeter



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